



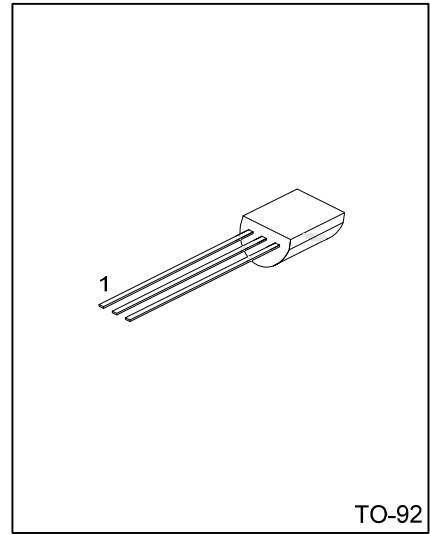
2SA1015

PNP SILICON TRANSISTOR

LOW FREQUENCY PNP AMPLIFIER TRANSISTOR

■ FEATURES

- * Collector-Emitter Voltage: $BV_{CEO} = -50V$
- * Collector Current up to 150mA
- * High h_{FE} Linearity
- * Complement to UTC 2SC1815



Lead-free: 2SA1015L
Halogen-free: 2SA1015G

■ ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
2SA1015-x-T92-B	2SA1015L-x-T92-B	2SA1015G-x-T92-B	TO-92	E	C	B	Tape Box
2SA1015-x-T92-K	2SA1015L-x-T92-K	2SA1015G-x-T92-K	TO-92	E	C	B	Bulk

<p>2SA1015L-x-T92-B</p> <p>(1)Packing Type (2)Package Type (3)Rank (4)Lead Plating</p>	<p>(1) B: Tape Box, K: Bulk (2) T92: TO-92 (3) x: refer to Classification of h_{FE} (4) G: Halogen Free, L: Lead Free Plating, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATING (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-150	mA
Base Current	I _B	-50	mA
Collector Dissipation	P _C	400	mW
Junction Temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55 ~ +125	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

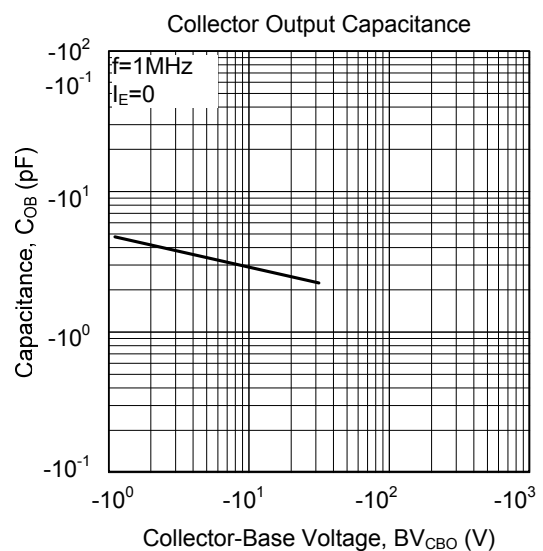
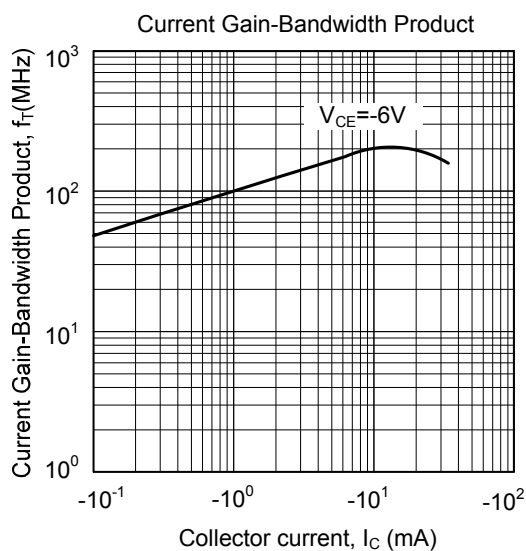
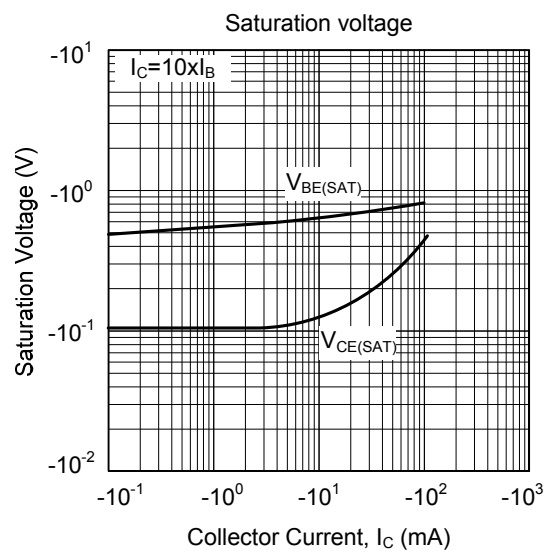
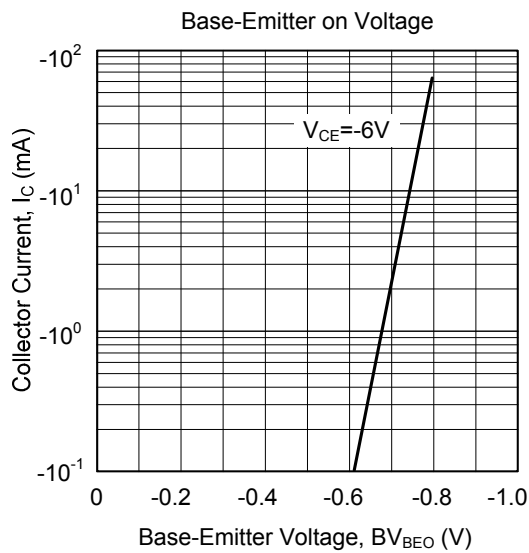
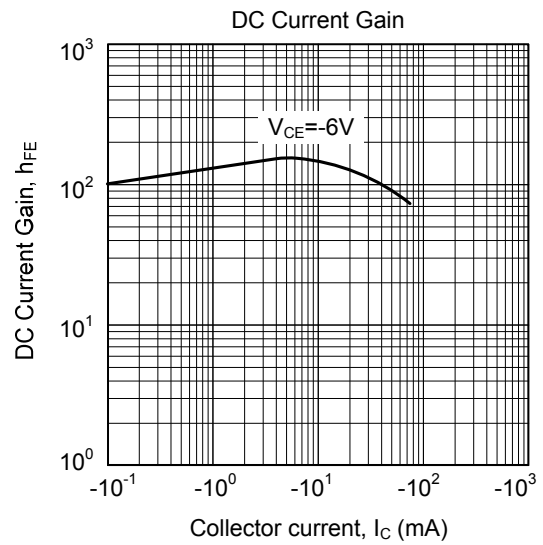
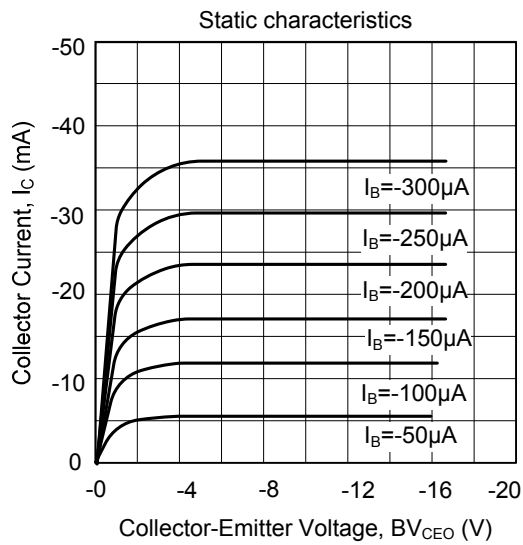
■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-10mA, I _B =0	-50			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-10μA, I _C =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-50V, I _E =0			-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC Current Gain	h _{FE1}	V _{CE} =-6V, I _C =-2mA	120		700	
	h _{FE2}	V _{CE} =-6V, I _C =-150mA	25			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-100mA, I _B =-10mA		-0.1	-0.3	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-100mA, I _B =-10mA			-1.1	V
Output Capacitance	C _{OB}	V _{CB} =-10V, I _E =0, f=1MHz		4.0	7.0	pF
Current Gain Bandwidth Product	f _T	V _{CE} =-10V, I _C =-1mA	80			MHz
Noise Figure	NF	V _{CE} =-6V, I _C =-0.1mA, R _G =1kΩ, f=100Hz		0.5	6	dB

■ CLASSIFICATION OF h_{FE1}

RANK	Y	GR	BL
RANGE	120-240	200-400	350-700

■ TYPICAL CHARACTERISTICS



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